

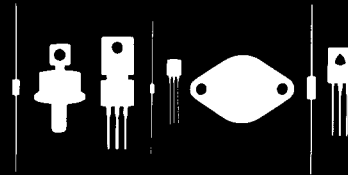
Central
Semiconductor Corp.

Central
Semiconductor Corp.

Central
Semiconductor Corp.

Central
Semiconductor Corp.

145 Adams Avenue
Hauppauge, New York 11788



2N6497

2N6498

2N6499

NPN SILICON
POWER TRANSISTOR

JEDEC TO-220 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N6497, 2N6498, 2N6499 types are Silicon NPN Power Transistors designed for high voltage amplifier applications.

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$)

	SYMBOL	2N6497	2N6498	2N6499	UNITS
Collector-Base Voltage	V_{CBO}	350	400	450	V
Collector-Emitter Voltage	V_{CEO}	250	300	350	V
Emitter-Base Voltage	V_{EBO}		6.0		V
Collector Current	I_C		5.0		A
Collector Current (Peak)	I_{CM}		10		A
Base Current	I_B		2.0		A
Power Dissipation	P_D		80		W
Operating and Storage					
Junction Temperature	T_J, T_{stg}		-65 to +150		$^\circ\text{C}$
Thermal Resistance	θ_{JC}		1.56		$^\circ\text{C/W}$

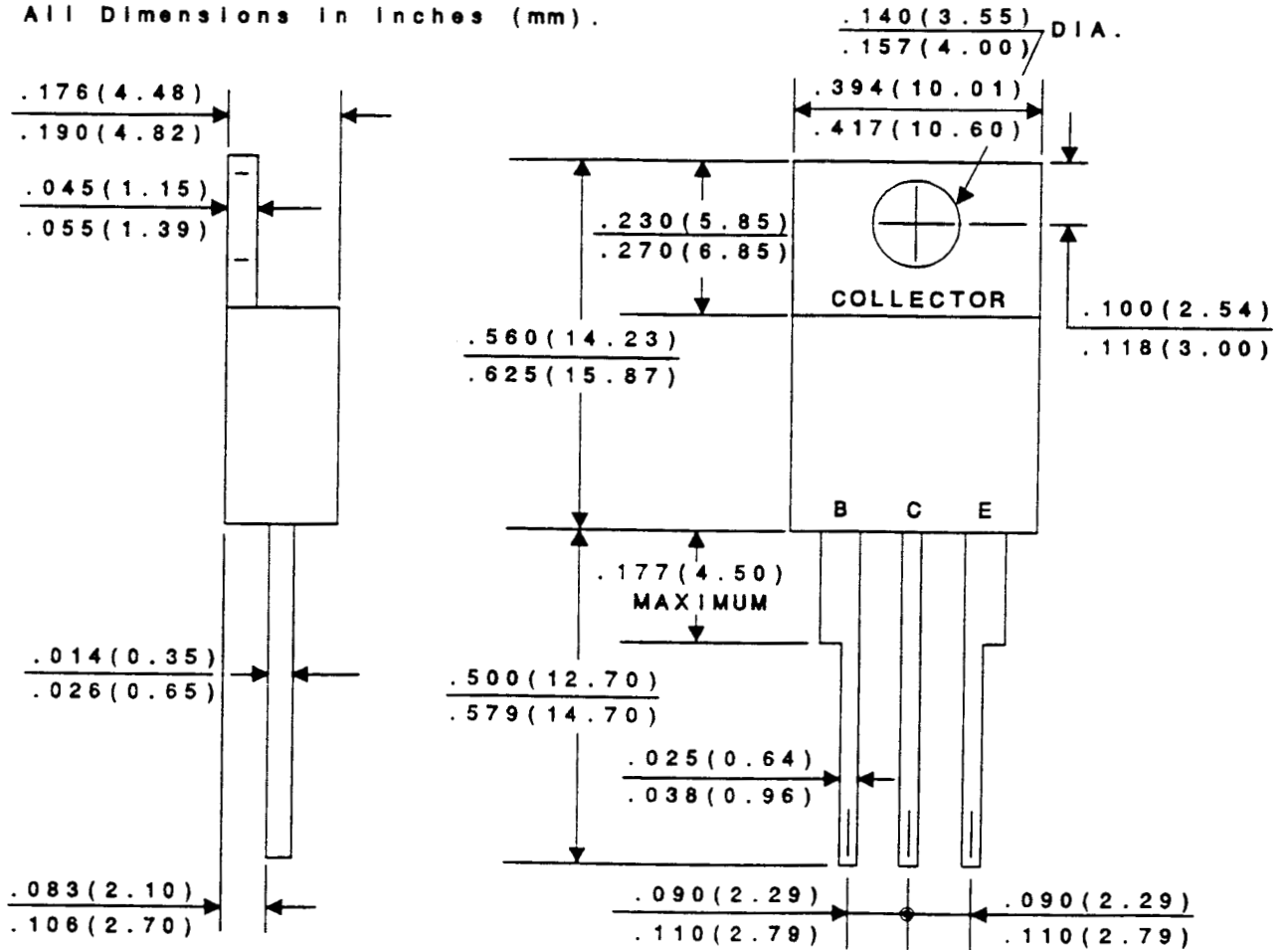
ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N6497		2N6498		2N6499		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I_{CEX}	$V_{CE} = \text{Rated } V_{CBO}, V_{BE} = 1.5\text{V}$		1.0		1.0		1.0	mA
I_{CEX}	$V_{CE} = \frac{1}{2} \text{Rated } V_{CBO}, V_{BE} = 1.5, T_C = 100^\circ\text{C}$		10		10		10	mA
I_{EBO}	$V_{BE} = 6.0\text{V}$		1.0		1.0		1.0	mA
BV_{CEO}	$I_C = 25\text{mA}$	250		300		350		V
$V_{CE(SAT)}$	$I_C = 2.5\text{A}, I_B = 500\text{mA}$		1.0		1.25		1.5	V
$V_{CE(SAT)}$	$I_C = 5.0\text{A}, I_B = 2.0\text{A}$		5.0		5.0		5.0	V
$V_{BE(SAT)}$	$I_C = 2.5\text{A}, I_B = 500\text{mA}$		1.5		1.5		1.5	V
$V_{BE(SAT)}$	$I_C = 5.0\text{A}, I_B = 2.0\text{A}$		2.5		2.5		2.5	V
h_{FE}	$V_{CE} = 10\text{V}, I_C = 2.5\text{A}$	10	75	10	75	10	75	
h_{FE}	$V_{CE} = 10\text{V}, I_C = 5.0\text{A}$	3.0		3.0		3.0		
f_T	$V_{CE} = 10\text{V}, I_C = 250\text{mA}, f = 1.0\text{MHz}$	5.0		5.0		5.0		MHz
C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 100\text{kHz}$		150		150		150	pF
t_r	$V_{CC} = 125\text{V}, I_C = 2.5\text{A}, I_{B1} = 0.5\text{A}$		1.0		1.0		1.0	μs
t_s	$V_{CC} = 125\text{V}, I_C = 2.5\text{A}, V_{BE} = 5.0\text{V}$							
	$I_{B1} = I_{B2} = 0.5\text{A}$		2.5		2.5		2.5	μs
t_f	$V_{CC} = 125\text{V}, I_C = 2.5\text{A}, I_{B1} = I_{B2} = 0.5\text{A}$		1.0		1.0		1.0	μs

(OVER)

MECHANICAL DIMENSIONS

All Dimensions in inches (mm).



Central[™]
Semiconductor Corp.

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824
www.centalsemi.com

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.